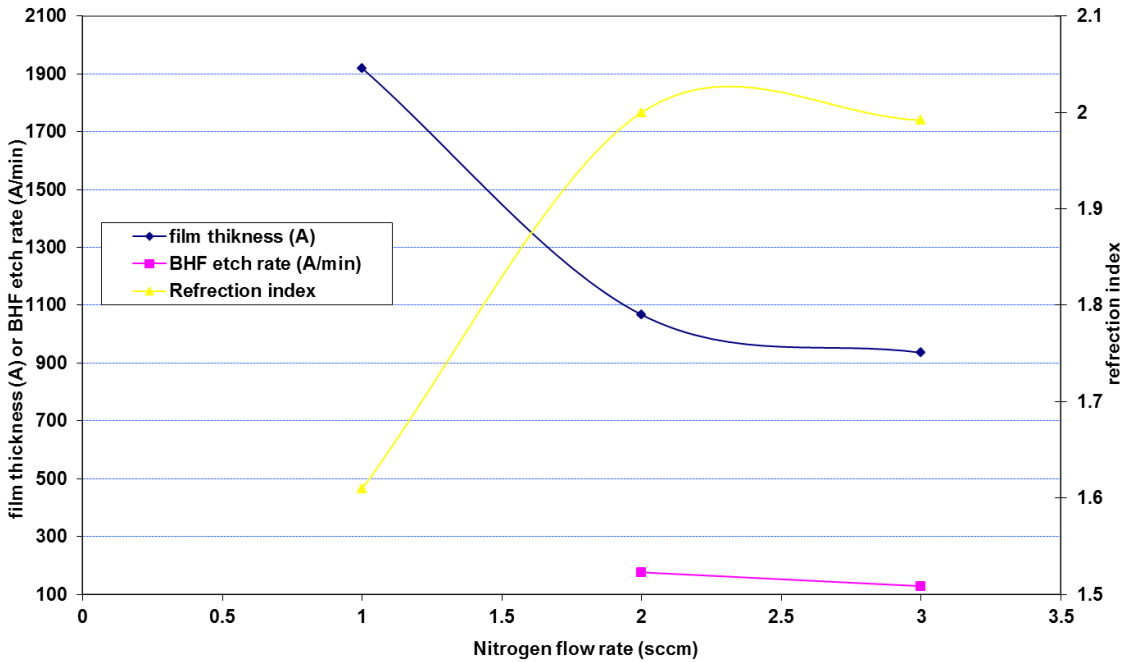


SiN Reactive Sputtering – N2 Flow Data AJA1

Thickness - Index - Etch Rate – vs N2 flow: 1 hour: Ar 25sccm; 200W RF; Bias 10W; 3mT; Ht/Tilt 25/9

SiNx film thickness, BHF etch rate and refraction index vs. N2 gas flow rate
(Bias:10W; Gun:200W; WD:25; Tilt: 9; Pressure:3mT; Ar gass flow rate:25sccm; time:1h)

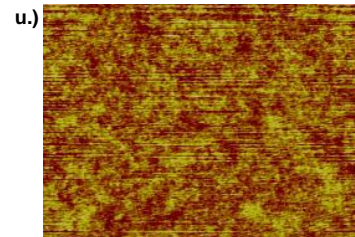
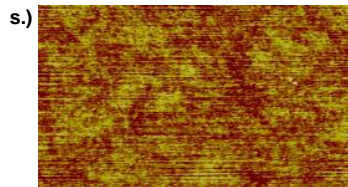
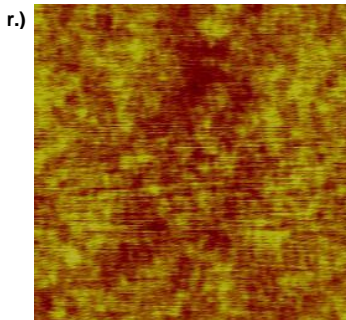


AFM – vs N2 flow: 1 hour: Ar 25sccm; 200W RF; 3mT; Ht/Tilt 25/9; Room T

AFM Measurements SiN AJA1

Ar-25sccm, 3mT, 200W, 1 hour, Ht/Tilt 25/9

Gas flow	Bias	name	roughness in nm		
			R _q	R _a	R _{max}
1 N ₂	10 W	r	0.0454	0.0361	0.3600
2 N ₂	10 W	s	0.0748	0.0593	1.1700
3 N ₂	10 W	u	0.0769	0.0608	0.7050



Thickness - Index - vs RF Power: 1 hour: N2/Ar 2.5/25sccm; Bias 10W; 3mT; Ht/Tilt 25/9

